

SECTION I. (AMENDMENTS TO THE CLAIMS)

A listing of claims 1-33 of the present application, with markings showing amendments made herein, is provided below:

Claims 1-23. (Cancelled).

Claim 24 (Cancelled).

Claim 25 (Currently amended) The electrical contact of Claim 24 33 wherein said silicon-containing semiconductor material comprises single crystal Si, polycrystalline Si, SiGe, amorphous Si or a silicon-on-insulator (SOI).

Claims 26-27 (Cancelled).

Claim 28 (Currently amended) The electrical contact of Claim 24 33 wherein said substrate is doped.

Claim 29 (Currently amended) The electrical contact of Claim 24 33 wherein said substrate includes a p⁺ silicon area.

Claim 30 (Currently amended) The electrical contact of Claim 24 33 wherein said substrate includes an n⁺ silicon area.

Claim 31 (Currently amended) The electrical contact of Claim 24 33 wherein said at least one additive is C, Al, Sc, Ti, V, Cr, Mn, Fe, Co, Cu, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, or Ir or Pt.

Claim 32 (Previously presented) An electrical contact to a region of a silicon-containing substrate comprising a substrate having an exposed region of a silicon-containing

semiconductor material; and a first layer of Ni monosilicide, wherein said substrate and said first layer are separated by a Si-Ge interlayer and said first layer of Ni monosilicide comprises at least one additive that is Ti, V, Cr, Nb, Rh, Ta, Re or Ir.

Claim 33 (Previously presented) An electrical contact to a region of a silicon-containing substrate comprising a substrate having an exposed region of a silicon-containing semiconductor material; and a first layer of Ni monosilicide, wherein said substrate and said first layer are separated by a Si-Ge interlayer and said first layer of Ni monosilicide comprises at least one additive selected from the group consisting of C, Al, Sc, Ti, V, Cr, Mn, Fe, Co, Y, Zr, Nb, Mo, Ru, Rh, Pd, In, Sn, La, Hf, Ta, W, Re, Ir, Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Tb and Lu.